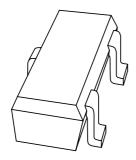
## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## PDTA143XK

PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$ 

Product specification

2002 Jan 15





## PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

### PDTA143XK

#### **FEATURES**

- Built-in bias resistors
- 250 mW total power dissipation
- Package size 2.9 × 1.5 × 1.15 mm
- · Simplification of circuit design
- Reduces number of components and required PCB area.

#### **APPLICATIONS**

- General purpose switching and amplification
- · Inverter and interface circuits
- · Circuit driver.

#### **DESCRIPTION**

PNP resistor equipped transistor in a SOT346 (SC-59) plastic package.

#### **MARKING**

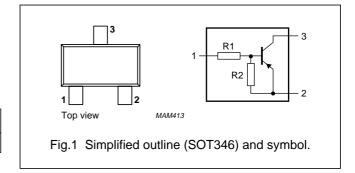
TYPE NUMBER	MARKING CODE		
PDTA143XK	25		

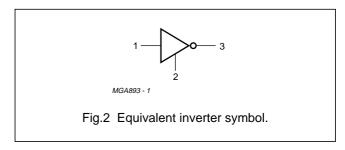
#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-50	V
Io	output current (DC)	-100	mA
R1	bias resistor	4.7	kΩ
R2	bias resistor	10	kΩ

#### **PINNING**

PIN	DESCRIPTION	
1	base/input	
2	emitter/ground (+)	
3	collector/output	





# PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

PDTA143XK

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-10	V
Vi	input voltage				
	positive		_	+7	V
	negative		_	-20	V
Io	output current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; note 1	500	K/W	

#### Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT346 in the SC18 Data Handbook".

<sup>1.</sup> For mounting conditions, see "Thermal considerations and footprint design for SOT346 in the SC18 Data Handbook".

# PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

PDTA143XK

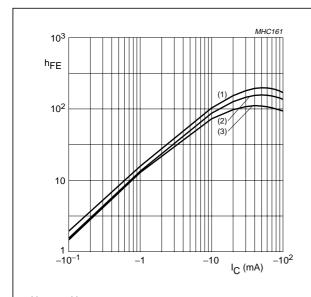
#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-0.6	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	50	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	_	-0.3	V
V <sub>i(on)</sub>	input on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -20 \text{ mA}$	-2.5	_	_	V
R1	input resistor		3.3	4.7	6.1	kΩ
R2	resistor ratio		1.7	2.1	2.6	
R1						
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	3	рF

## PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

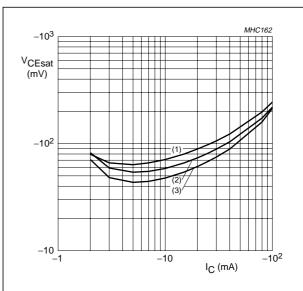
### PDTA143XK



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = 100 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -40 \, ^{\circ}C$ .

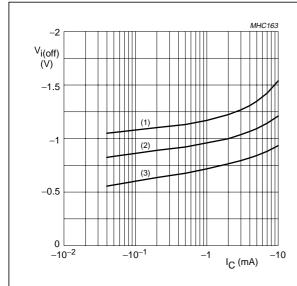
Fig.3 DC current gain as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

- (1)  $T_{amb} = 100 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -40 \, ^{\circ}C$ .

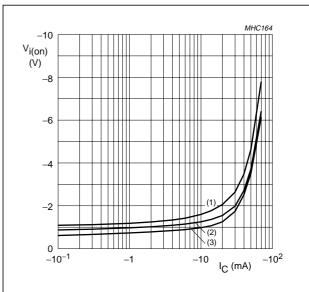
Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -40 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \,^{\circ}C$ .
- (3)  $T_{amb} = 100 \, ^{\circ}C$ .

Fig.5 Input-off voltage as a function of collector current; typical values.



 $V_{CE} = -0.3 \text{ V}.$ 

- (1)  $T_{amb} = 100 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \,^{\circ}C$ .
- (3)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig.6 Input-on voltage as a function of collector current; typical values.

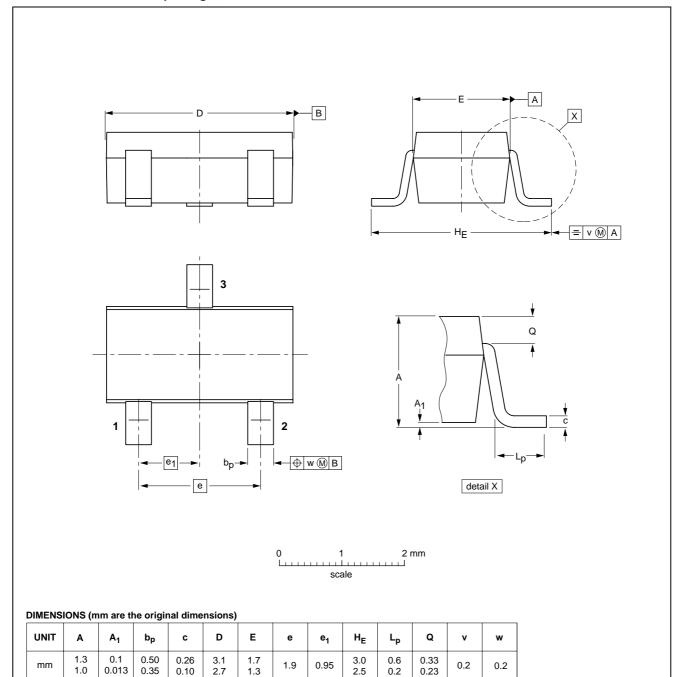
## PNP resistor-equipped transistor;

PDTA143XK  $R1 = 4.7 \text{ k}\Omega$ ,  $R2 = 10 \text{ k}\Omega$ 

#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

**SOT346** 



OUTLINE	REFERENCES		EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT346		TO-236	SC-59			98-07-17

2002 Jan 15 6

## PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 10 k $\Omega$

PDTA143XK

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For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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